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(54) Title of the Invention: **Preventing shorting of adjacent devices**
Abstract Title: **Preventing shorting of adjacent devices**

(57) Embodiments of the present invention provide a method of preventing electrical shorting of adjacent semiconductor devices. The method includes forming a plurality of fins (101-104) of a plurality of field-effect transistors on a substrate (109); forming at least one barrier structure (162) between a first (102) and a second (103) fin of the plurality of fins; and growing an epitaxial film (181-188) from the plurality of fins, the epitaxial film extending horizontally from sidewalls of at least the first and second fins and reaching the barrier structure situating between the first and second fins.

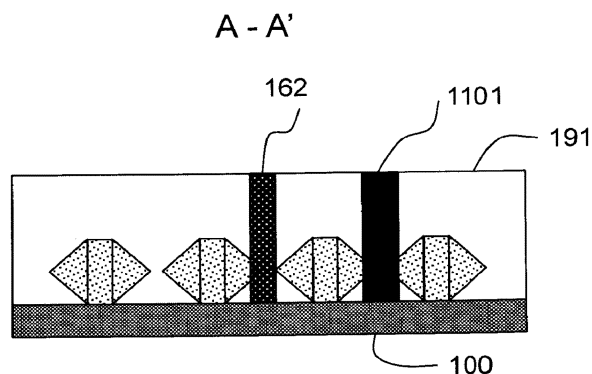


FIG. 10C

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